## **CLAIMS**

What is claimed is:

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1	A method	of forming a	a laver over	' a guhgfrate	comprising:
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depositing a layer of a first reactive species over the substrate;

chemically reacting the layer of the first reactive species with a second reactive species to create a first product; and

preferentially desorbing an unreacted reactive species leaving a layer of the first product.

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- 2. The method, as recited in claim 1, wherein the depositing of a layer deposits a monolayer.
- 3. The method, as recited in claim 2, wherein the depositing of a layer is by simple vapor deposition.
  - 4. The method, as recited in claim 3, wherein the simple vapor deposition is preformed by vaporizing a solid or liquid by heating.
- 5. The method, as recited in claim 4, wherein the unreacted reactive species that is desorbed is the first reactive species.

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- 6. The method, as recited in claim 5, wherein the step of desorbing the unreacted first reactive species, comprises heating the layer.
  - 7. The method, as recited in claim 6, further comprising:
- 5 cooling the layer after preferentially desorbing the unreacted first reactive species;

depositing a second layer of the first reactive species;

chemically reacting the layer of the first reactive species with the second reactive species to create the first product; and

preferentially desorbing unreacted first reactive species leaving a second layer of the first product.

- 8. The method, as recited in claim 1, wherein the depositing of a layer is by simple vapor deposition.
- 9. The method, as recited in claim 8, wherein the unreacted reactive species that is desorbed is the first reactive species.
- 10. The method, as recited in claim 1, wherein the unreacted reactive species that is desorbed is the first reactive species.
  - 11. The method, as recited in claim 1, wherein the step of desorbing the unreacted reactive species comprises heating the layer.

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12. The method, as recited in claim 1, further comprising:

cooling the layer after preferentially desorbing the unreacted first reactive species;

depositing a second layer of the first reactive species;

5 chemically reacting the layer of the first reactive species with the second reactive species to create the first product; and

preferentially desorbing unreacted reactive species leaving a second layer of the first product.

13. A thin film of a plurality of layers over a substrate, wherein each layer is individually formed by the method, comprising:

depositing a layer of a first reactive species over the substrate;

chemically reacting the layer of the first reactive species with a second reactive species to create a first product; and

preferentially desorbing an unreacted reactive species leaving a layer of the first product.

14. The thin film, as recited in claim 13, wherein the depositing of a layer deposits a monolayer.

15. The thin film, as recited in claim 14, wherein the depositing of a layer is by simple vapor deposition.

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- 16. The thin film, as recited in claim 15, wherein the simple vapor deposition is preformed by vaporizing a solid or liquid by heating.
- 17. The thin film, as recited in claim 16, wherein the unreacted reactive
  5 species that is desorbed is the first reactive species.